3.3 V 32-bit bus transceiver with 30 Ω termination resistors; 3-state

Rev. 01 — 24 January 2007

Product data sheet

1. General description

The 74LVTH322245 is a high-performance BiCMOS product designed for V_{CC} operation at 3.3 V. The 74LVTH322245 is designed with 30 Ω series resistance in both the HIGH and LOW states of the output. This design reduces line noise in applications such as memory address drivers, clock drivers, and bus receivers/transmitters. The 74LVTH322245 is a 32-bit transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions. The device features four output enable (n \overline{OE}) inputs for easy cascading and four send/receive (nDIR) inputs for direction control. Pin n \overline{OE} controls the outputs so that the buses are effectively isolated. Bus hold on data inputs eliminates the need for external pull-up resistors to hold unused inputs.

2. Features

- 32-bit bidirectional bus interface
- 3-state buffers
- Output capability: +12 mA and -12 mA
- TTL input and output switching levels
- Input and output interface capability to systems at 5 V supply
- Bus hold data inputs eliminate need for external pull-up resistors to hold unused inputs
- Live insertion and extraction permitted
- Outputs include series resistance of 30 Ω making external resistors unnecessary
- Power-up 3-state
- No bus current loading when output is tied to 5 V bus
- Latch-up protection:
 - JESD78 Class II level A exceeds 500 mA
- ESD protection:
 - HBM JESD22-A114E exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V

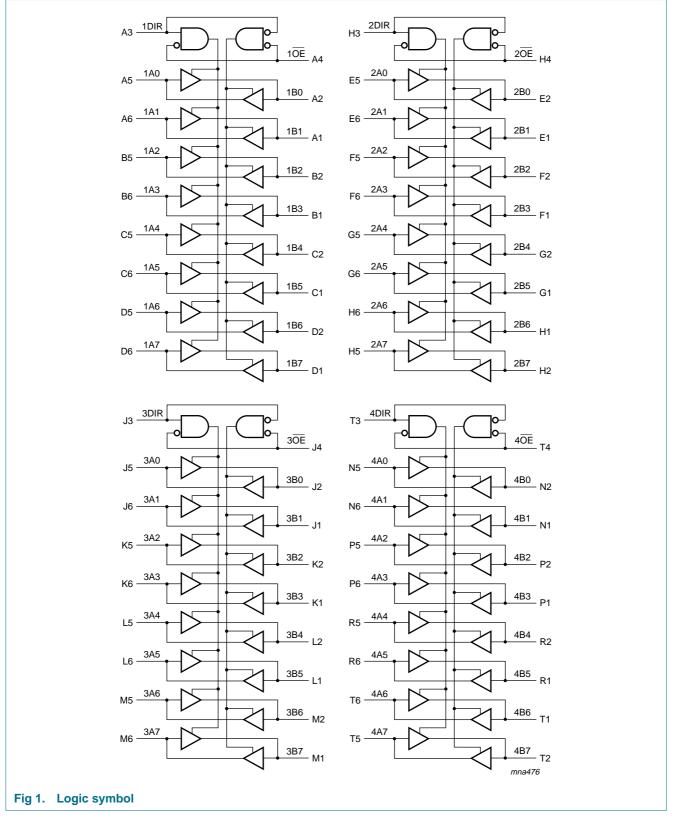
3. Ordering information

| Table 1. Ordering information | | | | | | | | |
|---------------------------------------|-------------------|---------|---|----------|--|--|--|--|
| Type number | Package | | | | | | | |
| | Temperature range | Name | Description | Version | | | | |
| 74LVTH322245EC | –40 °C to +125 °C | LFBGA96 | plastic low profile fine-pitch ball grid array package; 96 balls; body $13.5 \times 5.5 \times 1.05$ mm | SOT536-1 | | | | |



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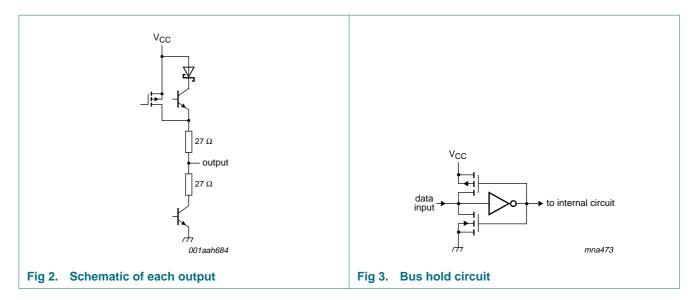
4. Functional diagram



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5. Pinning information

5.1 Pinning

| | | | | | | | | | | | | | | | | | r | mna475 |
|--------|------------|------|------|-----|-----|-----|-----|-----|-----|------|------|-----|-----|-----|-----|-----------------|-----|--------|
| | | 6 | 1A1 | 1A3 | 1A5 | 1A7 | 2A1 | 2A3 | 2A5 | 2A6 | 3A1 | 3A3 | 3A5 | 3A7 | 4A1 | 4A3 | 4A5 | 4A6 |
| | | 5 | 1A0 | 1A2 | 1A4 | 1A6 | 2A0 | 2A2 | 2A4 | 2A7 | 3A0 | 3A2 | 3A4 | 3A6 | 4A0 | 4A2 | 4A4 | 4A7 |
| | | 4 | 10E | GND | Vcc | GND | GND | Vcc | GND | 20E | 30E | GND | Vcc | GND | GND | V _{CC} | GND | 40E |
| | | 3 | 1DIR | GND | Vcc | GND | GND | Vcc | GND | 2DIR | 3DIR | GND | Vcc | GND | GND | VCC | GND | 4DIR |
| | | 2 | 1B0 | 1B2 | 1B4 | 1B6 | 2B0 | 2B2 | 2B4 | 2B7 | 3B0 | 3B2 | 3B4 | 3B6 | 4B0 | 4B2 | 4B4 | 4B7 |
| | | 1 | 1B1 | 1B3 | 1B5 | 1B7 | 2B1 | 2B3 | 2B5 | 2B6 | 3B1 | 3B3 | 3B5 | 3B7 | 4B1 | 4B3 | 4B5 | 4B6 |
| | | | A | В | С | D | E | F | G | Н | J | к | L | М | N | Р | R | т |
| Fig 4. | Pin config | gura | tion | | | | | | | | | | | | | | | |

5.2 Pin description

Table 2.Pin description

| Symbol | Ball | Description |
|-------------------------------|--------------------------------|-------------------------------------|
| nDIR (n = 1 to 4) | A3, H3, J3, T3 | direction control |
| $n\overline{OE}$ (n = 1 to 4) | A4, H4, J4, T4 | output enable input (active LOW) |
| 1A[0:7] | A5, A6, B5, B6, C5, C6, D5, D6 | input or output |
| 1B[0:7] | A2, A1, B2, B1, C2, C1, D2, D1 | input or output |
| 2A[0:7] | E5, E6, F5, F6, G5, G6, H6, H5 | input or output |
| 2B[0:7] | E2, E1, F2, F1, G2, G1, H1, H2 | input or output |
| 3A[0:7] | J5, J6, K5, K6, L5, L6, M5, M6 | input or output |
| 3B[0:7] | J2, J1, K2, K1, L2, L1, M2, M1 | input or output |
| 74LVTH322245_1 | | © NXP B.V. 2008. All rights reserve |

| Table 2. | Pin description continued | | |
|-----------------|---------------------------|---|-----------------|
| Symbol | | Ball | Description |
| 4A[0:7] | | N5, N6, P5, P6, R5, R6, T6, T5 | input or output |
| 4B[0:7] | | N2, N1, P2, P1, R2, R1, T1, T2 | input or output |
| GND | | B3, B4, D3, D4, E3, E4, G3, G4, K3, K4, M3, M4, N3, N4, R3, R4 | ground (0 V) |
| V _{CC} | | C3, C4, F3, F4, L3, L4, P3, P4 | supply voltage |

6. Functional description

| Table 3. | Function selection ^[1] | | |
|----------|-----------------------------------|--------------|-----------|
| Input | | Input/output | |
| nOE | nDIR | nAn | nBn |
| L | L | nAn = nBn | inputs |
| L | Н | inputs | nBn = nAn |
| Н | Х | Z | Z |

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state

7. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V)^{[1][2]}

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------|-----------------------------|-----------------|------|------|
| V _{CC} | supply voltage | | -0.5 | +4.6 | V |
| VI | input voltage | | <u>[3]</u> –0.5 | +7.0 | V |
| Vo | output voltage | output in OFF or HIGH-state | <u>[3]</u> –0.5 | +7.0 | V |
| I _{IK} | input clamping current | V ₁ < 0 V | -50 | - | mA |
| Ι _{ΟΚ} | output clamping current | V _O < 0 V | -50 | - | mA |
| l _O | output current | output in LOW-state | - | 128 | mA |
| | | output in HIGH-state | -64 | - | mA |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | - | 150 | °C |
| Тj | junction temperature | | - | 150 | °C |

[1] Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond indicated under <u>Section 8 "Recommended operating conditions"</u> is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

[2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.

[3] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

8. Recommended operating conditions

| Table 5. | Recommended | operating | conditions |
|----------|-------------|-----------|------------|
|----------|-------------|-----------|------------|

| Symbol | Parameter | Conditions | Min | Тур | Мах | Unit |
|-----------------------|-------------------------------------|-----------------|--------------|-----|------|------|
| V _{CC} | supply voltage | | 2.7 | - | 3.6 | V |
| VI | input voltage | | 0 | - | 5.5 | V |
| I _{OH} | HIGH-level output current | | -12 | - | - | mA |
| I _{OL} | LOW-level output current | | - | - | 12 | mA |
| T _{amb} | ambient temperature | in free air | -40 | - | +85 | °C |
| $\Delta t / \Delta V$ | input transition rise and fall rate | outputs enabled | - | - | 10 | ns/V |
| P _{tot} | total power dissipation | | <u>[1]</u> _ | - | 1000 | mW |

[1] Above 70 $^\circ\text{C}$ the value of P_tot derates linearly with 1.8 mW/K.

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------|---|----------------|-------|------|------|
| Γ _{amb} = – | 40 °C to +85 °C <u>[1]</u> | | | | | |
| V _{IK} | input clamping voltage | $V_{CC} = 2.7 \text{ V}; \text{ I}_{IK} = -18 \text{ mA}$ | -1.2 | -0.85 | - | V |
| V _{IH} | HIGH-level input voltage | | 2.0 | - | - | V |
| V _{IL} | LOW-level input voltage | | - | - | 0.8 | V |
| V _{ОН} | HIGH-level output voltage | $V_{CC} = 3.0 \text{ V}; \text{ I}_{OH} = -12 \text{ mA}$ | 2.0 | 2.5 | - | V |
| V _{OL} | LOW-level output voltage | $V_{CC} = 3.0 \text{ V}; \text{ I}_{OL} = 12 \text{ mA}$ | - | 0.3 | 0.8 | V |
| I | input leakage current | control pins | | | | |
| | | V_{CC} = 3.6 V; V_{I} = V_{CC} or GND | - | 0.1 | ±1 | μA |
| | | $V_{CC} = 0 V \text{ or } 3.6 V; V_{I} = 5.5 V$ | - | 0.1 | 10 | μA |
| | | input/output data pins; V_{CC} = 3.6 V | [2] | | | |
| | | $V_I = V_{CC}$ | - | 0.5 | 10 | μA |
| | | $V_{I} = 0 V$ | -5 | -0.1 | - | μA |
| I _{OFF} | power-off leakage current | V_{CC} = 0 V; V_{I} or V_{O} = 0 V to 4.5 V | - | 0.1 | ±100 | μA |
| I _{LO} | output leakage current | output HIGH; $V_0 = 5.5 \text{ V}$; $V_{CC} = 3.0 \text{ V}$ | - | 75 | 125 | μΑ |
| I _{O(pu/pd)} | power-up/power-down output current | $\label{eq:V_CC} \begin{array}{l} V_{CC} \leq 1.2 \ \text{V}; \ \text{V}_{O} = 0.5 \ \text{V} \ \text{to} \ \text{V}_{CC}; \\ \text{V}_{I} = \text{GND} \ \text{or} \ \text{V}_{CC}; \ \text{n} \overline{\text{OE}} = \text{don't care} \end{array}$ | <u>[4]</u> | 40 | ±100 | μΑ |
| BHL | bus hold LOW current | $V_{CC} = 3 \text{ V}; \text{ V}_{I} = 0.8 \text{ V}$ | 75 | 135 | - | μA |
| I _{BHH} | bus hold HIGH current | $V_{CC} = 3 \text{ V}; \text{ V}_{I} = 2.0 \text{ V}$ | - | -135 | -75 | μA |
| I _{BHLO} | bus hold LOW overdrive current | V_{CC} = 0 V to 3.6 V; V_{I} = 3.6 V | <u>[3]</u> 500 | - | - | μΑ |
| внно | bus hold HIGH overdrive current | V_{CC} = 0 V to 3.6 V; V_{I} = 3.6 V | [3] _ | - | -500 | μA |
| сс | supply current | V_{CC} = 3.6 V; V_I = GND or V_{CC} ; I_O = 0 A | | | | |
| | | outputs HIGH | - | 0.14 | 0.24 | mA |
| | | outputs LOW | - | 8.4 | 12 | mA |
| | | outputs disabled | [5] _ | 0.14 | 0.24 | mA |

| At recom | At recommended operating conditions; voltages are referenced to GND (ground = 0 V). | | | | | | | | | |
|------------------|---|--|--------------|-----|-----|------|--|--|--|--|
| Symbol | Parameter | Conditions | Min | Тур | Мах | Unit | | | | |
| ΔI_{CC} | additional supply current | per input pin; V_{CC} = 3 V to 3.6 V; one input at V_{CC} – 0.6 V; other inputs at V_{CC} or GND | <u>[6]</u> _ | 0.1 | 0.2 | mA | | | | |
| CI | input capacitance | control pins; $V_0 = 0 V \text{ or } 3.0 V$ | - | 3 | - | pF | | | | |
| C _{I/O} | input/output capacitance | input/output data pins; outputs disabled; V_{CC} = 3.6 V; I_O = 0 A; V_I = GND or V_{CC} | - | 9 | - | pF | | | | |

Table 6. Static characteristics ... continued

[1] All typical values are at V_{CC} = 3.3 V and T_{amb} = 25 °C unless otherwise specified.

[2] Unused pins at V_{CC} or GND.

This is the bus-hold overdrive current required to force the input to the opposite logic state. [3]

- [4] This parameter is valid for any V_{CC} between 0 V and 1.2 V with a transition time of up to 10 ms. From V_{CC} = 1.2 V to V_{CC} = $3.3 \text{ V} \pm 0.3 \text{ V}$ a transition time of 100 μs is permitted. This parameter is valid for T_{amb} = 25 °C only.
- I_{CC} is measured with outputs pulled to V_{CC} or GND. [5]
- [6] This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND.

10. Dynamic characteristics

Table 7. **Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for load circuit see Figure 7.

| Symbol | Parameter | Conditions | Min | Typ <mark>[1]</mark> | Max | Unit |
|-----------------------|-------------------------------------|--|-----|----------------------|-----|------|
| T _{amb} = -4 | 0 °C to +85 °C | | | | | |
| t _{PLH} | LOW to HIGH propagation delay | nAn to nBn or nBn to nAn; see <mark>Figure 5</mark> | | | | |
| | | $V_{CC} = 2.7 V$ | - | - | 3.9 | ns |
| | | V_{CC} = 3.0 V to 3.6 V | 1.0 | 2.5 | 3.5 | ns |
| t _{PHL} | HIGH to LOW propagation delay | nAn to nBn or nBn to nAn; see <u>Figure 5</u> | | | | |
| | | $V_{CC} = 2.7 V$ | - | - | 3.9 | ns |
| | | V_{CC} = 3.0 V to 3.6 V | 1.0 | 2.2 | 3.5 | ns |
| t _{PZH} | OFF-state to HIGH propagation delay | nOE to nAn or nBn; see Figure 6 | | | | |
| | | $V_{CC} = 2.7 V$ | - | - | 6.4 | ns |
| | | V_{CC} = 3.0 V to 3.6 V | 1.5 | 3.5 | 5.3 | ns |
| t _{PZL} | OFF-state to LOW propagation delay | nOE to nAn or nBn; see Figure 6 | | | | |
| | | $V_{CC} = 2.7 V$ | - | - | 5.0 | ns |
| | | V_{CC} = 3.0 V to 3.6 V | 1.5 | 3.2 | 4.4 | ns |
| t _{PHZ} | HIGH to OFF-state propagation delay | nOE to nAn or nBn; see Figure 6 | | | | |
| | | $V_{CC} = 2.7 V$ | - | - | 5.1 | ns |
| | | V_{CC} = 3.0 V to 3.6 V | 1.5 | 3.5 | 4.8 | ns |
| t _{PLZ} | LOW to OFF-state propagation delay | nOE to nAn or nBn; see Figure 6 | | | | |
| | | $V_{CC} = 2.7 V$ | - | - | 5.9 | ns |
| | | $V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ | 1.5 | 4.3 | 6.7 | ns |

[1] All typical values are at V_{CC} = 3.3 V and T_{amb} = 25 °C.

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11. Waveforms

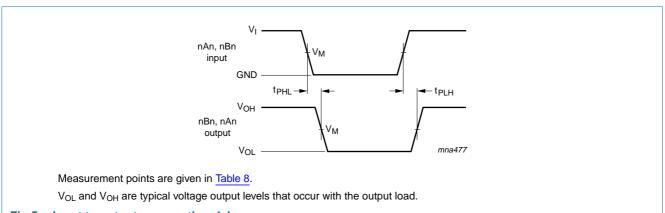


Fig 5. Input to output propagation delays

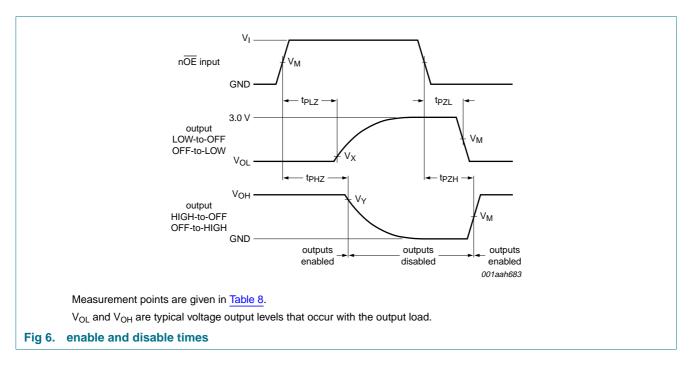


Table 8.Measurement points

| Supply voltage | Input | Output | | |
|-----------------|----------------|----------------|-------------------------|-------------------------|
| V _{CC} | V _M | V _M | V _X | V _Y |
| 2.7 V to 3.6 V | 1.5 V | 1.5 V | V _{OL} + 0.3 V | V _{OH} – 0.3 V |

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74LVTH322245

3.3 V 32-bit bus transceiver with 30 Ω termination resistors; 3-state

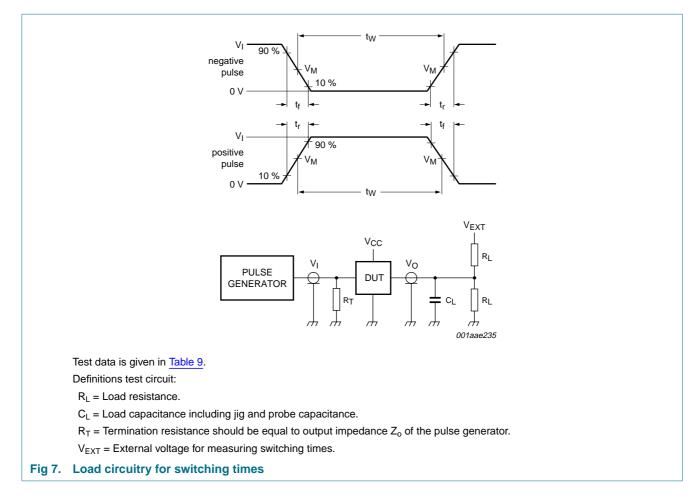
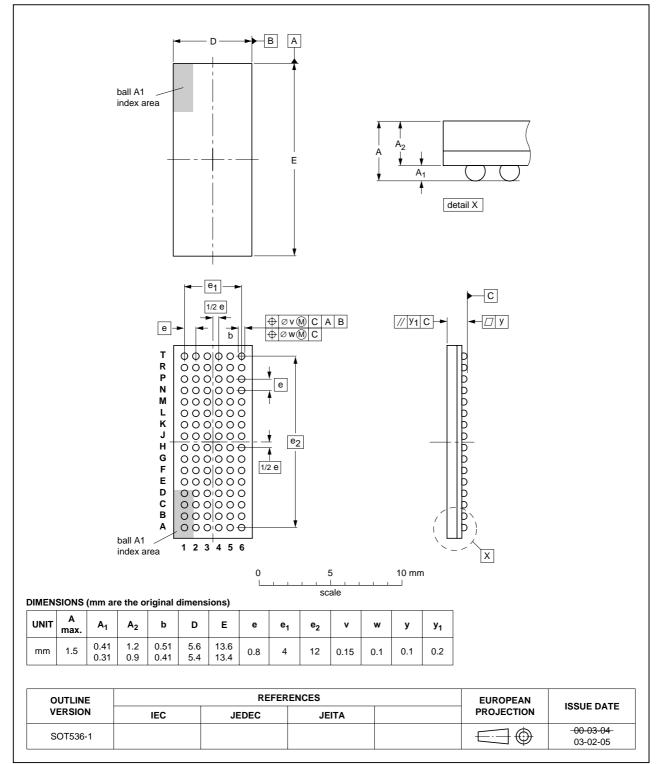


Table 9.Test data

| Input | | | Load | | V _{EXT} | | | |
|-------|----------------|----------------|---------------------------------|-------|------------------|-------------------------------------|-------------------------------------|-------------------------------------|
| VI | f _i | t _W | t _r , t _f | RL | CL | t _{PHZ} , t _{PZH} | t _{PLZ} , t _{PZL} | t _{PLH} , t _{PHL} |
| 2.7 V | \leq 10 MHz | 500 ns | \leq 2.5 ns | 500 Ω | 50 pF | GND | 6 V | open |

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12. Package outline



LFBGA96: plastic low profile fine-pitch ball grid array package; 96 balls; body 13.5 x 5.5 x 1.05 mm SOT536-1

Fig 8. Package outline SOT536-1 (LFBGA96)

13. Abbreviations

| Table 10. | Abbreviations | | |
|-----------|---|--|--|
| Acronym | Description | | |
| BiCMOS | Bipolar Complementary Metal-Oxide Semiconductor | | |
| DUT | Device Under Test | | |
| ESD | ElectroStatic Discharge | | |
| HBM | Human Body Model | | |
| MM | Machine Model | | |
| TTL | Transistor-Transistor Logic | | |

14. Revision history

| Table 11. Revision history | | | | | |
|----------------------------|--------------|--------------------|---------------|------------|--|
| Document ID | Release date | Data sheet status | Change notice | Supersedes | |
| 74LVTH322245_1 | 20080124 | Product data sheet | - | - | |

15. Legal information

15.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
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74LVTH322245

3.3 V 32-bit bus transceiver with 30 Ω termination resistors; 3-state

17. Contents

| 1 | General description 1 |
|------|------------------------------------|
| 2 | Features 1 |
| 3 | Ordering information 1 |
| 4 | Functional diagram 2 |
| 5 | Pinning information 3 |
| 5.1 | Pinning 3 |
| 5.2 | Pin description 3 |
| 6 | Functional description 4 |
| 7 | Limiting values 4 |
| 8 | Recommended operating conditions 5 |
| 9 | Static characteristics 5 |
| 10 | Dynamic characteristics 6 |
| 11 | Waveforms 7 |
| 12 | Package outline 9 |
| 13 | Abbreviations |
| 14 | Revision history 10 |
| 15 | Legal information 11 |
| 15.1 | Data sheet status 11 |
| 15.2 | Definitions 11 |
| 15.3 | Disclaimers |
| 15.4 | Trademarks 11 |
| 16 | Contact information 11 |
| 17 | Contents 12 |

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